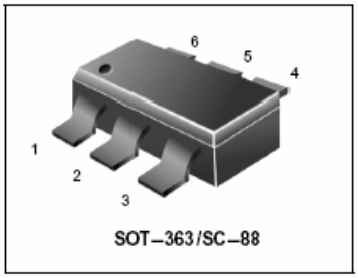
Power MOSFET

N-Channel/P-Channel SC-88

LBSS8402DW1T1G
S-LBSS8402DW1T1G

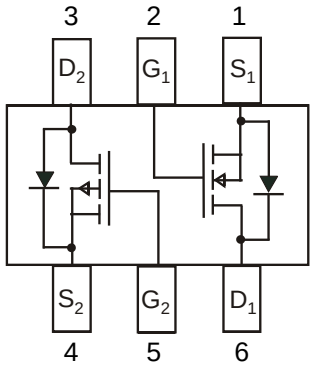
- We declare that the material of product are Halogen Free and compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



SOT–363/SC–88

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain–to–Source Voltage	V_{DSS}	50	Vdc
Gate–to–Source Voltage – Continuous	V_{GS}	± 20	Vdc
Drain Current – Continuous @ T_A = 25°C – Pulsed Drain Current ($t_p \le 10$ µs)	 I_D I_{DM}	 130 520	mA
Total Power Dissipation @ T_A = 25°C	P_D	380	mW
Operating and Storage Temperature Range	T_J, T_{stg}	– 55 to 150	°C
Thermal Resistance – Junction–to–Ambient	$R_{\theta JA}$	328	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	°C



ORDERING INFORMATION

Device	Marking	Shipping
LBSS8402DW1T1G S-LBSS8402DW1T1G	402	3000 Tape & Reel
LBSS8402DW1T3G S-LBSS8402DW1T3G	402	10000 Tape & Reel

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N-Channel

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–to–Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 µAdc)		$V_{(BR)DSS}$	50	–	–	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 25 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 50 Vdc, V_{GS} = 0 Vdc)		I_{DSS}	 – –	 – –	 0.1 0.5	µAdc
Gate–Source Leakage Current (V_{GS} = ± 20 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	–	–	±0.1	µAdc
ON CHARACTERISTICS (Note 1.)						
Gate–Source Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mAdc)		$V_{GS(th)}$	0.5	–	1.5	Vdc
Static Drain–to–Source On–Resistance (V_{GS} = 2.75 Vdc, I_D < 200 mAdc, T_A = –40°C to +85°C) (V_{GS} = 5.0 Vdc, I_D = 200 mAdc)		$r_{DS(on)}$	 – –	 5.6 –	 10 3.5	Ohms
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 25 Vdc, V_{GS} = 0, f = 1 MHz)	C_{iss}	–	42	–	pF
Output Capacitance	(V_{DS} = 25 Vdc, V_{GS} = 0, f = 1 MHz)	C_{oss}	–	15	–	
Transfer Capacitance	(V_{DG} = 25 Vdc, V_{GS} = 0, f = 1 MHz)	C_{rss}	–	3	–	
SWITCHING CHARACTERISTICS (Note 2.)						
Turn–On Delay Time	(V_{DD} = 30 Vdc, I_D = 0.2 Adc,)	$t_{d(on)}$	–	5	–	ns
Turn–Off Delay Time		$t_{d(off)}$	–	7	–	

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

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P-Channel

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–to–Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 µAdc)		$V_{(BR)DSS}$	50	–	–	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 25 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 50 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 50 Vdc, V_{GS} = 0 Vdc, T_J = 125°C)		I_{DSS}	 – – –	 – – –	 0.1 15 60	µAdc
Gate–Body Leakage Current (V_{GS} = ± 20 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	–	–	±100	nAdc
ON CHARACTERISTICS (Note 1.)						
Gate–Source Threaded Voltage (V_{DS} = V_{GS}, I_D = 250 µAdc)		$V_{GS(th)}$	0.8	–	2.0	Vdc
Static Drain–to–Source On–Resistance (V_{GS} = 5.0 Vdc, I_D = 100 mAdc)		$r_{DS(on)}$	–	5.0	10	Ohms
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 5.0 Vdc)	C_{iss}	–	30	–	pF
Output Capacitance	(V_{DS} = 5.0 Vdc)	C_{oss}	–	10	–	
Transfer Capacitance	(V_{DG} = 5.0 Vdc)	C_{rss}	–	5.0	–	
SWITCHING CHARACTERISTICS (Note 2.)						
Turn–On Delay Time	(V_{DD} = –15 Vdc, I_D = –2.5 Adc, R_L = 50 Ω)	$t_{d(on)}$	–	13	–	ns
Rise Time		t_r	–	6	–	
Turn–Off Delay Time		$t_{d(off)}$	–	16	–	
Fall Time		t_f	–	3	–	
Gate Charge		Q_T	–	6000	–	pC

1. Pulse Test: Pulse Width 300 µs, Duty Cycle 2%.
2. Switching characteristics are independent of operating junction temperature.

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N-Channel TYPICAL ELECTRICAL CHARACTERISTICS

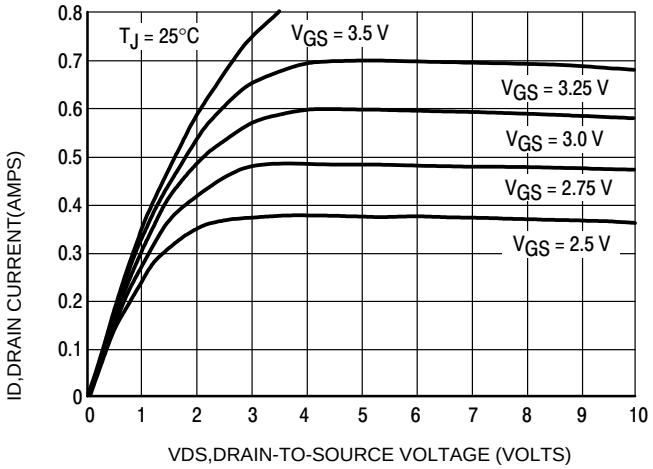

Figure 1. On–Region Characteristics

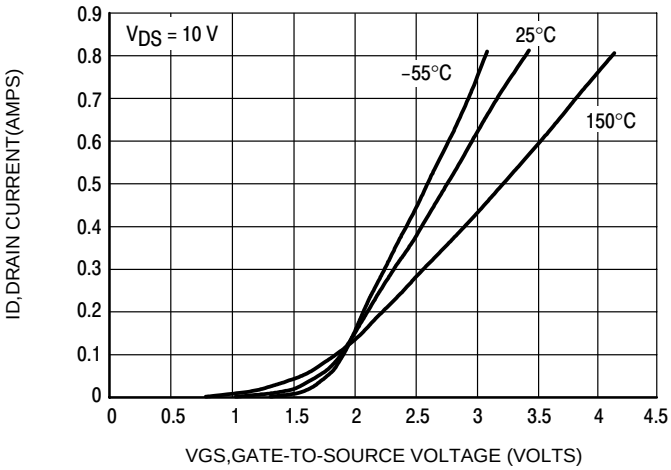

Figure 2. Transfer Characteristics

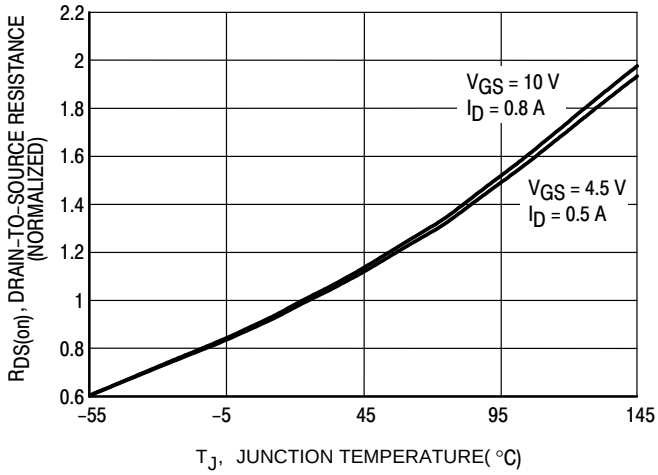

Figure 3. On–Resistance Variation with Temperature

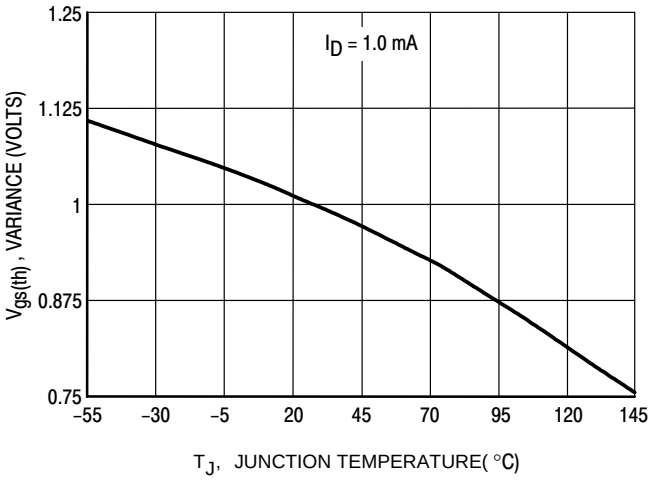

Figure 4. Threshold Voltage Variation with Temperature

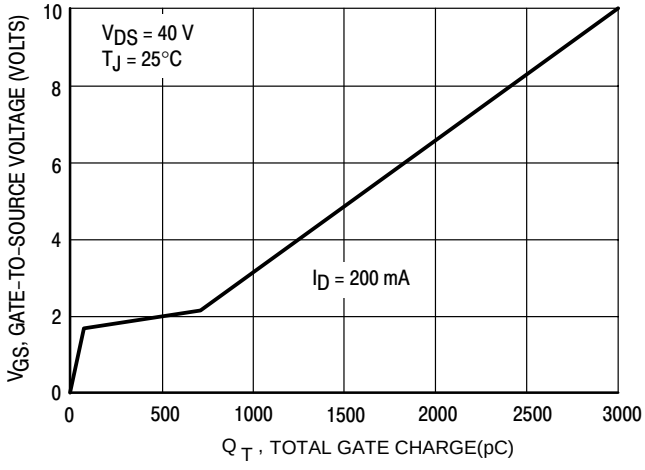

Figure 5. Gate Charge

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P-Channel TYPICAL ELECTRICAL CHARACTERISTICS

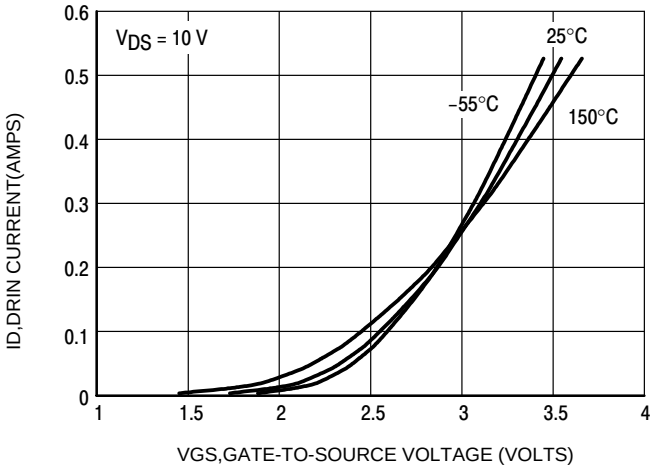


Figure 1. Transfer Characteristics

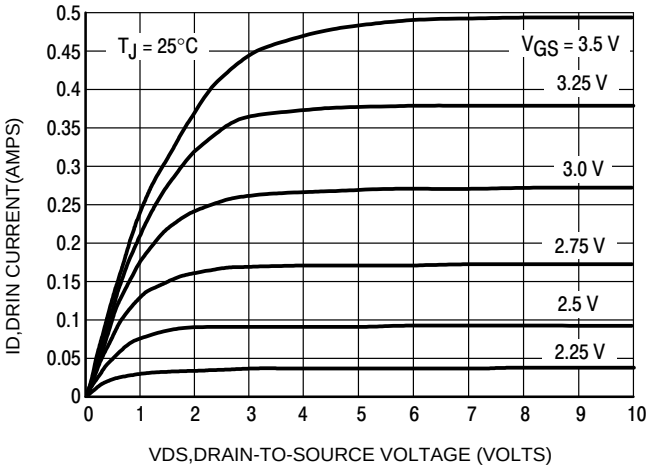


Figure 2. On–Region Characteristics

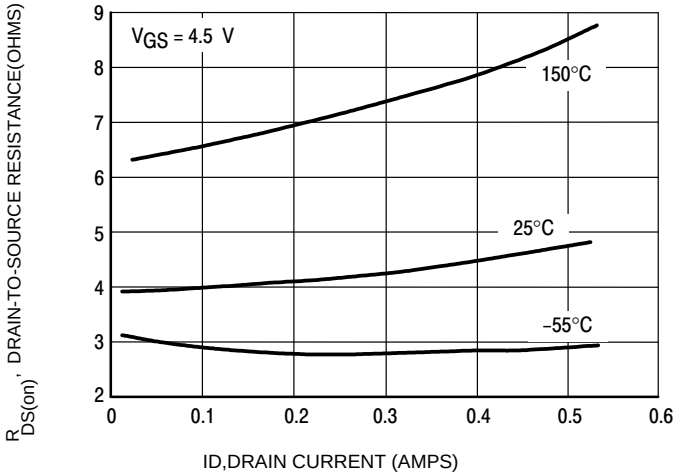


Figure 3. On–Resistance versus Drain Current

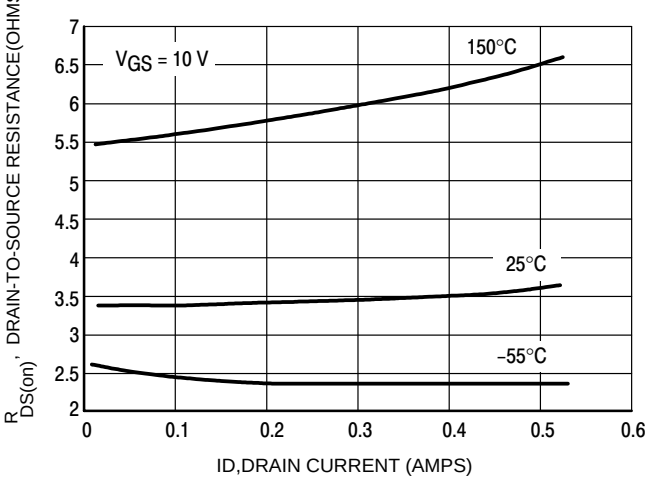


Figure 4. On–Resistance versus Drain Current

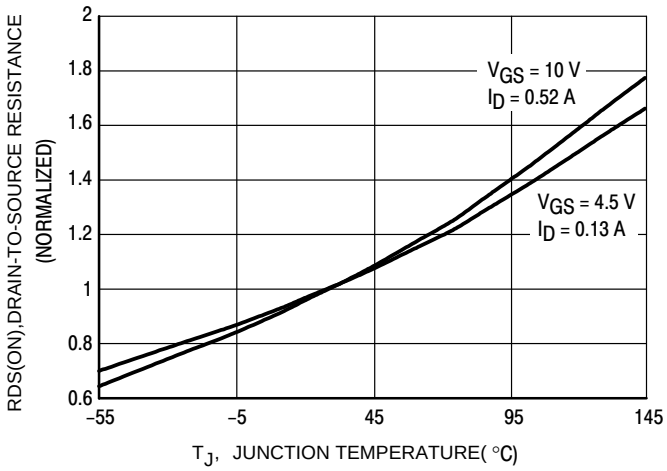


Figure 5. On–Resistance Variation with Temperature

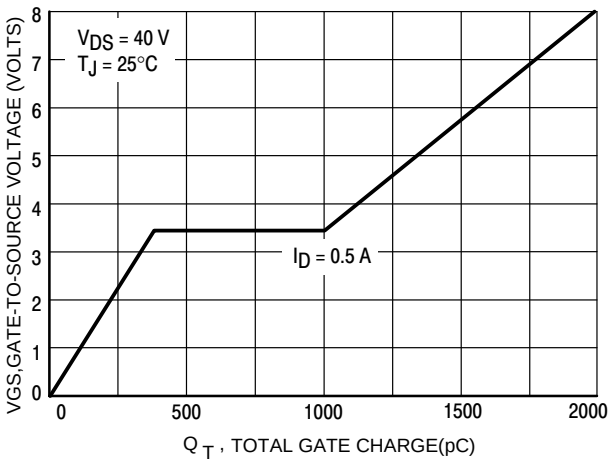
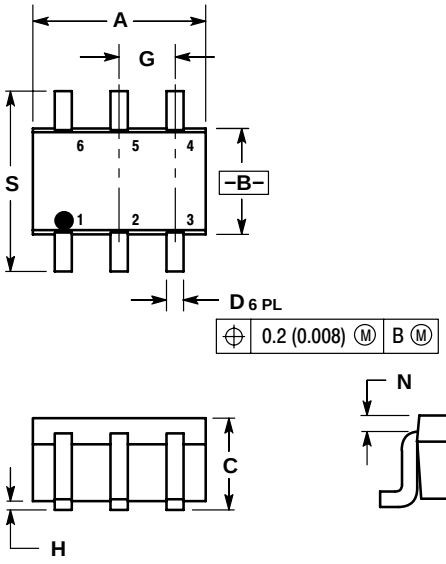


Figure 6. Gate Charge

LBSS8402DW1T1G , S-LBSS8402DW1T1G

SC−88 (SOT−363)
CASE 419B−02
ISSUE T



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B−01 OBSOLETE, NEW STANDARD 419B−02.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	−−−	0.004	−−−	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

SOLDERING FOOTPRINT*